The MMIC (Microwave Monolithic Integrated Circuits) are wide band integrated circuits often used as simple amplifiers, they are designed to replace the transistor and help the designer to build RF amplifiers. Loosely but realistically MMICs are the evolution of thick film ICs (in fact in this section are listed also some old thick film amplifiers).

Without going into technical detail, because it is available a very big quantity of documentation, in few words we can say that the MMIC is used to simplify an amplification chain without worrying about possible self oscillations, instability, impedance mismatching or the bias, the MMIC can solve all these problems. With MMICs design is made easier, securer and more repeatable, all models are matched nearly at 50 / 75  $\Omega$  of input impedance.

MMICs are used to ease design process and improve the RF circuits repeatability, their implementation is very easy so the Ohm's law only is needed to calculate the other components of the circuits. Here are explained the 3 classical circuits for power supply and decuopling.

- A) MMICs normally use the 4 leads configuration, input, output with power supply and two gound connections. Rarely some types have a separate power supply lead, some others have the bias lead to adjust the current.
- B) The decoupling capacitors are used only to block the DC power supply, the value must be a short circuit at the desired frequency. Cb bypass capacitor is used only to short circuit the RF to avoid self oscillations of the MMIC and to avoid that possible noise can enter in the MMIC, the choice of this capacitor is very important if the MMIC has a high gain or there are more than one amplification stage.
- C) The bias resistor has the purpose of lowering the power supply voltage from the available value to the right power supply value of the MMIC (for example from Vc 12V to Vd 5V)
- D) It is always suggested to use an inductance, in this case the decoupling is increased on the power supply, it can be avoided in the case that the calculated R is so high that it is enough to obtain a good decoupling (for example R > 150 / 200  $\Omega$ ). Instead the inductance must be inserted when the power supply voltage is similar to the working voltage of the MMIC (that is if Vd = Vc), in fact in this case it is not possible to insert the bias resistor on power supply and the decoupling is made by the inductance itself. The same if the power supply resistor has a too low value (up to 80 / 100  $\Omega$ ).
- E) To improve performaces of these devices, especially at higher frequencies, it is suggested to use SMD or with very short leads components in particular for all ground connections



NOTE : in case of high value inductances (> 10  $\mu$ H) should be considered a little residual resistance due to the wire of the inductance itself.

Given the huge variety of MMIC devices, but especially the wide variety of performances and technical specifications, we decided to group all these devices in a table of 3 pages. To facilitate the search we have divided them according to their main characteristics:

Low cost and general purpose	low cost
Low noise	NF < 3 dB
High dynamic	medium output power +10 / +17 dBm
High output power	> 17 dBm > 50 mW
Very flat gain	it can be used on instrumentation to have flat gain on wide band
High reverse insulation	high S12, ie high reverse insulation between output and input, for example as buffer for VCOs and oscillators
Variable gain	with pin for gain control
Differential amplifier	
Low voltage power supply	< 3.5 V
Other special feateures	see table below

This table is used for a fast search of the device, other features will be then shown on following pages with prices and eventually a test report for MMICs considered more interesting.

# **MMICs selection guide**

function	cod.	CASE	FREC	<b>Q.</b> GHz	g	ain	out p	ower	1	NF	3° ord	ler IP	pw	r sup.
Tanotion			mın	- max	max	dB min	dBm a	t GHz	dB a	it GHz	dBm a	t GHz	V	mA
	AG101	SMD	60MH	z-3GHz	15	11	+15	1	2.4	2	+28/+3	21	4.5	50
	ERA 1	plastic	up to a	8 GHz	12	10	+11.5	2			+26	2	3.6	40
	ERA 2	plastic	up to a	8 GHz	16	12	+12.4	2			+26	2	3.6	40
	SNA 286	plastic	DC	6	15	11	+14	2	5.7	2	+29	2	3.8	50
	INA 34063	SMD	DC	3	± 2	0 dB	+8	2	4.5	2	+18	2	3	30
	INA 52063	SMD	DC	2.5	23	16	+8	1	3.5	0.1	+20	1	5	30
	LMX 2119	SMD	1.5	2.5	2	20	+23,5	2					3.6	350
	MAR 1-MSA0186	plas-cer	DC	2.5	18	9	+2	0.5	5.5	0.5	+14	0.5	5	17
	MAR 2 - RAM2	plas-cer	DC	3.5	12.5	8	+5	1			+17	1	5	25
CENEDAL	MAR 3	plas-cer	DC	3	12.5	8	+10	1			+23	1	5	35
GENERAL	MAR 4	plast.cer	DC	2	9	8	+12.5	1			+25.5	1	5.2	50
PURPOSE	MAR 6	plas-cer	DC	1.5	20	13	+2	1	3	0.5	+14	0.5	3.5	16
	MAR 8	plast-cer	DC	2	27	16	+12.5	1	3.3	1	+27	1	7.8	36
and	MAV 11	plastic	DC	2	13	7.5	+17.5	0.5	3.6	0.5	+30	0.5	5.5	60
	MGA 72543	SMD	up to	6 GHz	17	9	+12	5	1.5	4	+10	2	3	20
LOW	MGA 85563	SMD	0,8	6	19	15	+1	3	1.6 c band	on all width	+12	3	3	20-30
COST	MSA 0711 e 0735	SMD	DC	3	13	8	+5.5	1	5	1	+18	1	4	22
	RF 2472	SMD	DC	6	21	9	+2	2	1.4 2	1.5 5	+18		3	6
	SGA 2186	plastic	DC	5	10	7.5	+7	1.5	4.4	2	+19.5	2	2.2	20
	SGA 2286	plastic	DC	5	15	10	+7	2	3.5	2	+19	2	2.2	20
	SGA 2386	plastic	DC	5	18	10	+7.5	2	3.3	2	+20	1.5	2.7	20
	SGA 2486	plastic	DC	5	21	11	+7.5	2	3.3	2	+20	2	2.7	20
	SGA 3286	plastic	DC	5	15	10.5	+11.5	1.5	3.8	2	+24	2	2.6	35
	SH 225	special	1 - 90	0 MHz	21	19	+2	0.5	5.5	0.5			24	23
	μΡС 2709Τ	SMD	DC	2.5	22	19	+8	0.5	5	1			5	25
	μPC 2771T	SMD	DC	2.5	21	18	+11.5	1	6	1			3	35

6				FRE	<b>Q</b> . GHz		gain	out	power	N	IF	3° ord	ler IP	pwr	sup.
tunctio	n	cod.	CASE	min	- max	max	dB min	dBm	at GHz	dB a	t GHz	dBm a	t GHz	V	mA
	#	AG101	SMD	60MH	z-3GHz	15	11	+15	1	2.4	2	+28/+3	21	4.5	50
	#	AM1 - AG102	SMD	60MH	z-3GHz	15	11	+18	2	2.4	2	+33/+3	61	4.4	60-80
	#	AM50-0003	SMD	800-1	000MHz		15	+18		1.2				3-8	20-60
	#	AM50-0004	SMD	1.4 -:	2 GHz		14	+18		1.4				3-8	20-45
		INA03184	plas-cer	DC	4	25	12	-1	1	2.5	1.5	+7	1.5	3-5	10
	#	MAALSS0034	SMD	70MH	z-3GHz	15	9	+23	2	1.6	2	+36	2	5	88
		MAAM12031 + 032	SMD	1.7 - 2	2 GHz	20	13	+2	/ +7	1.7	/ 1.8	+2 /	+7	5	5/8
LOW	#	MGA 62563	SMD	up to	2.5GHz	23	13	+	17	0.9	1	+32	.5	3-5	60
	#	MGA 72543	SMD	up to	6 GHz	17	9	+12	5	1.5	4	+10	2	3	20
NOISE	#	MGA 81563	SMD	0.5	6	12.5	5 10	+14.8	3	2.7	3	+27	2	3	42
		MGA 85563	SMD	0,8	6	19	15	+1	3	1.6 o band	n all width	+12	3	3	20-30
NF ≤ 3 dB		MGA 86563	SMD	0.5	6 (8)	22	15	+4.3	4	1.7	4	+15	2.4	5	14
		MGA 86576	ceramic	0.5	10	23	12	+7	2.5	1.8	6	+16	4	4-10	16
# = high		MAR 6	plas-cer	DC	1.5	20	13	+2	1	3	0.5	+14	0.5	3.5	16
dynamic	#	MGF 7002	metallic	0.8	1.9	18	16	+10	1.6	2.5		+22	1	10/-6	90
	#	MGF 7003	ceram	0.1	1.9	12	10	+10	1.8	<2.5	4.5	+24	1	3	30
		RF 2472	SMD	DC	6	21	9	+2	2	1.4 2	1.5 5	+18		3	6
	#	SGA 3586	plastic	DC	5	26	13	+ 13.5	5 1.5	2.5	2	+25.5	1.5	3.3	35
	#	SGA 4586	plastic	DC	5	26	10	+16 /	+13	1,8	1	+27	2	3.6	45
	#	SGA 5586	plastic	DC	4	26	14	+18 /	+15	2.6	2	+30	1.5	3.9	60
	#	UTO 1043	metallic	5-130	0 MHz	11	8.7	+9	1	2.5	0.5	+22	0.5	12-15	25
		ERA 1	plastic	up to	8 GHz	12	10	+11.5	2			+26	2	3.6	40
		ERA 2	plastic	up to	8 GHz	16	12	+12.4	2			+26	2	3.6	40
		ERA 3	plastic	up to	8 GHz	22	12	+11.5	2			+23	2	3.5	35
		ERA 4	plastic	up to	8 GHz	14	12	+16.8	2			+32	2	5	65
		INA 10386	plastic	DC	4	26	14	from +	12 to +14	3.8	1.5	+23	1.5	6	45
_		MGA 64135		0.5	10	14	8.6	+12 up	<u>r sGHZ</u>		4		<u> </u>	8-11	50
HIGH		MGA 72543	SMD		6 GHZ	17	9	+12	2	1.5	4	+10	2	3	20
DYNAMI	С	MAD 2 VAM2		0.5	3	12.0		+14.0	1	2.1	3	+27	2 1	3	42
and					25	12.5	, 0 ; 8	+10	0.5			+22	1	4-0	35
MEDIUM		MAR4-MSA0436	ceramic	DC	3	8.5	, <u> </u>	+13	0.5			25.5	1	4-6	50
POWER	,	MAR8-MSA0870	plas-cer	DC	3	32	12	+13	0.5	3.3	1	+27	1	6-9	36
	•	NGA 286	plastic	DC	6	16	11	+15	2	3.4	2	+31	2	4	50
		SGA 3286	plastic	DC	5	15	10.5	+11.5	1.5	3.8	2	+24	2	2.6	35
≥ + 10dBm	n	SGA 3386	plastic	DC	5	18	11	+11.5	1.5	3.5	2	+24	1.5	2.6	35
( ≥ 10 mW	)	SGA 3486	plastic	DC	5	23	12	+12.5	2	3.2	2	+25	1.5	2.9	35
		SGA 3586	plastic	DC	5	28	13	+ 13.5	5 1.5	2.5	2	+25.5	1.5	3.3	35
		SGA 4186	plastic	DC	5	10	8	+ 13.5	5 1.5			+28 / +	25	3.2	45
		SGA 4586	plastic	DC	5	26	10	+16 /	+13	1,8	1	+27	2	3.6	45
		SGA 5586	plastic	DC	4	26	14	+18 /	+15	2.6	2	+30	1.5	3.9	60
		SNA 286	plastic	DC	6	15	11	+14	2			+29	2	3.8	50
		SNA 386	plastic	DC	4	22	15	+11	2	4.5	2	+23	2	3.8	35

3

# continue , MMIC selection guide

												1		1	
functio	า	cod.	CASE	FREC	<b>Q</b> . GHz	gain	dD min	out po	wer	NF dD o	+ CU-	3° ord		pwr s	sup.
	-			min -		max		dBm at	GHZ	aB a	CGHZ	uBm a		V	MA 60.00
	#	AWT - AGTUZ	SMD				II ar dual	$\pm 10$	ے 1 ب	2.4 0 MU	Z 25	/ +33/+	D D D D D D D D D D D D D D D D D D D	4.4	00-00
	#	CGY 2014	motallia	20 11				10/+20			2 + 30	/ +32 u		power	160
	#		nlactic	20-11 DC	6 (10)	20	10	+19/+20	ງ <u>0.</u> ອ	4	0.0	+32.5	0.0	5	65
	#		plastic		6 (10)	20	10.5	+10	2	4.5	1	+33	2	5	70
	-	CDD 405	piastic	10 5		11,0	10,5	+10	2	6	0.1	+30	2	5.5	70
		GPD 405		10-5	2 500	10	12	+10 20	0.4	10	1.0	+29	0.1	15	90
шец			SMD	100	2.000	13	20	+19 20	2001-0	4.0	1.0	+32	1	4.0	250
	#		SMD	70MH	2.5 2.5	15	20	+23,5	2	16	2	+36	2	5.0	200
POWER	#	MAAL330034	SMD	250 M		20	9	+23	24	2.5	2	+30	2	5	250
	#	MAV 44	o Ivi D		nz 4000	12	7.5	+20.5	2.4	2.5	2	+40	2	156	200
≥ +17 dBm	#	MGA 62562	S M D	UD to	2 50 47	13	1.0	+17.5	0.5	3.0	0.5	+30	0.5	4.5-0	60
(≥ 50 mW)	π	MGA 02505	SMD		2.5012	23	0	±17	2	0.9	2	+34	2.0	3-5	00 84
# - low		MGA 92563	SMD	0.4	6	21	17	+10	 1_2	2.2	2	+20	1 6	3	150
# = 10W	-	MDEIC 1950	SMD	0.0			17 or duol	$\pm 19$	1 - 3 1 + 100			(+29 /+22 d	I-U Pmout	5 Dowor	150
noise		NCA 496	S IVI D	powe	<u> </u>			10/+10			2 + 34	/ +32 u			00
		NGA 400 DM 2407	plastic plastic	200	0	10	20	+19/+10	0.372	4	2	+30/+	54	4.0	00 1 0V
	-	PIVI 2107	Pias siliu	2	2.0	20	20	+20/30	JK 2.4					+50 -	1.20
		RF 2140 DE 2174 2175	SMD				20 ar dual	+20 band 00(	1.0 1 dan (	900 N	 /山っょ	36/+3	23 dBm	4.5	400
	-	RF 2174 - 2175		do	7	11		10 Janu 900	ז anu i ר	000 1	II IZ Ŧ			57	70
		JITO 2012	metallic	500.2	/ 000MHマ	11	10	+10	1	1	5	+30	0.1-Z	0.7 15	100
	-		SMD	0.5	2 5	10	14	+ <u></u>	1	5.5	.5	+27	-33	5	85
			S IVI D	0.5	2.5	10 4	14	+10.2	2	5.5		+27		0	50
		ERA 1	plastic	DC	9-11	12-1	6 10 F	+12	2			+26	2	3.8	50
			plastic	DC	0	11,5	10,5	+18			4 5	+30	<u> </u>	5.5	70
		INA 03184	plas-cer	DC	4	25	12	-1	1	2.5	1.5	+/	1.5	3-5	10
		INA 10386	plastic		4	26	14	+12 to	+14	3.8	1.5	+23	1.5	6	45
VERT		NIGA 81563	ט ט ט ט ט ט ט very flat gain up to about 2 GHz								3	42			
FLAT							a far in		tation	and			Varia		
				ase,	particul	ar us		strumer		anu u-	profes	ssional	, vano	us typ	es
GAIN		GFA GFD	available	2 00		ligii p			- 2 G	пд				24	22
		SH 223	special	2 90		400 1	<u> </u>	+Z						24	23
		SINA 200			11at 101111	100 1			0.5	5	1			5	25
		μPC 27091	SMD		2.5	22	19	+11 5	0.0	5	1			5 2	20
		μες 2//11		DC	2.5	21		+11.5	I	0	ا مد:مد ا			3	30
		INA 34063	SMD	DC	3	± ∠	20 08		reverse		ation >	> 30 aB		3	30
HIGH	-	μρς 27091	SMD	DC	2.5	22	19	re	/. Insula	ation >	> 30dE	B low co	ost	5	25
REVERSE	•	MAX 2470 - 2175	SMD	10-50	0 MHz	13	15	re	v. insu	1. >50	dB VC	C buffe	er	3-5.5	5 6
	N	MGA 83563	SMD	0.5	6	21	17	insul. <	2GHz	>35d	B - >	2GHz	300B	3.3	150
1		SH 225		1- 900	MHz ve	ry flat	: amplifie	er with 40	DdB of	revers	se insu	ulation		24	23
	=	CGY 120	gain conti	ol ran	ge = 50 (	dB, ba	andwidtl	n up to 2	.5 GHz						
GAIN	-	IVA05208-14208	gain conti	ol ran	ge = 30 (	dB (I\	/A05208	3) 34 d	B (IVA	14208	) more	e spec.	see be	ow	
		RF 2145	high powe	er, gaiı	n control	rang	e = 40 d	В							
DIFFERENTIA	۱L	IVA 05208	SMD	DC	2	30	20		grou	ip dela	ay is w	vithin		4-6.5	5 35
amplifier		IVA 14208	SMD	DC	3	25	18			400	pSec			5-8	38
LOW		GPD 110 - INA340	63 - INA0	3184	- MAR	6 - M	AX	µPC 27	71			see r	nore d	etaileo	t
VOLTAGE		MGA 62563 + 7254	4 + 82563	+ 83	563 + 8	5563	- MGF	7003 -	MSA	07	sp	pecifica	ations i	n the i	next
< 3.5 V		SGA 2186 + 2286	+ 2386 +	3286	+ 3386	+ 34	86						pages	6	
		GPD 110	for very lo	ow fre	quencie	s stai	rting fro	m 50 - 1	00 KH	z up t	o 1.1	GHz , ۱	Vmin 2	.5 V	
with		MGA 64135	high perf	orman	ices up t	to10 (	GHz, hi	gh outpu	it level	, HI-R	REL pr	ofessio	onal cei	amic o	case
VVILII		MGA 72543	it has a s	witch	inside to	excl	ude it fr	om the o	circuit						
onesic		MGA 86576	for micro	wave,	ceramic	case	e, works	s up to 1	0 GHz	, low	noise				
special		MSA 0910	for instru	menta	tion, lim	ited b	out ultra	-flat gair	<u>0.1-4 וו</u>	GHz	HI- R	EL spe	cial ca	se	
f f		IDA 07318	1.5 Gbit of	driver	for laser	or le	d, TX d	atas on	fiber o	ptic					
teatures		MAR1-MSA 0185	very low	VSWF	R up to 3	3 GHz	z on bot	h input a	and ou	tput p	orts				
		VNA 25	it has alre	eady ii	nside tw	o dc	block ca	apacitors	s and t	he bia	as net	work			

## Low noise high dynamic M.M.I.C.

The following products AM-1, AG-101G, AG-102 and MAALSS0034 are MMICs from the prestigious Watkins Johanson and MaCom brand for high dynamic range applications (+16 to +22 dBm), but with a very low noise (1,6 to 2,5 dBNF). The case is the consolidated SOT89 that guaratees a good dissipation even when it is used with a fair current. These MMICs implement GaAs-FET technology and they are suitable for many applications, especially as post-amplifier after very low noise stages.

For example, suppose to use them after a MGA-62563 MMIC or a MAR6, you will get some more decibel of gain greatly increasing the dynamic with an output level up to +16 / +22 dBm. Another interesting application is as a driver for a broadband power module like BGD802, in fact the BGD802 to give the output power of 1 W it requires about 30 mW of input, so these MMICs are the right choice also as TX driver. The application diagram is extremely simple, just the usual dc-block capacitor and a choke for power supply are needed.

In conclusion, the AM-1, AG-102, AG101G and MAALSS0034 MMICs can be used for all applications requiring good dynamic associated with a low noise, as drivers for a higher power stage but also as a buffer stage with medium gain suitable for any need.

MMIC: A	AM-1	AG-102	AG-101G	MA	ALSS0034, some applications
MGA-62563	+	AM-1 AG-101G	AG-102 MAALSS0034	=	ultra low noise high dynamic aplifier
⇔					gain 20 - 30 dB output +16 / +22 dBm , OIP3 +33 / +36dBm
MAR-6		AM-1 AG-101G	AG-102 MAALSS0034		low noise amplifier
	+		<b>Ģ</b>	=	50 / 70MHz - 1.5 GHz NF 2.5 - 3.5 dB gain 22 - 35 dB output + 18 dBm , OIP3 +26dBm
AM-1 AG-102 AG-101G MAALSS0034		wide band examp	d power module, ble BGD-802		wide band power amplifier
	+	1	RFHIC	=	output 0,5 - 1 W #
			2F3632		gain about 30 dB #
		-			# depending on the used power module
AM-1 AG-102 AG-101G MAALSS0034		pow	ver transistor or		medium-high power amplifier
	+	pov pc	or wer MMIC		Depending on the used final
	AC 10	2	Solder to a	little -	
AG-101G MA	AG-10 ALSS00	)34 am	copper ground   for dissipa	plain ation	>180 nH +3,5 / +5V typ. +4,5V 65 - 85 mA in ■I = = = = = = = = = = = = = = = = = =
	0	M	MIC : AM-1	AG	-102 AG-101G MAALSS0034
Frequency	range				60 – 3000 MHz
Gain					10 – 15 dB
Ouput P	1dB		from +	16 dBm	n to + 22 dBm (depending on model)
	ビン Nure		+39	arw /	+33 GBM (depending on model)
	Juie				1,0 – 2.0 db

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6

#### high performances professional MMICs

These particular ICs are used in professional field, such as final stage or driver in laboratory RF signal generators, military RF-VHF front-end receivers for example Watkins - Johnson, Rohde & Schwarz, A class amplifiers, and laboratory and so on. They have better features than common MMICs, such as a low input-output VSWR, constant phase throughout the whole band with a fair group delay, P1dB, IP3 and IP2 specified and guaranteed, etc... They are typically used in wide band circuits and also where is the need of a very fast response as recovery time.

Some have the two dc-block capacitors already inside which greatly facilitates their use, other models have not the capacitors inside (which have to be added externally) this is an advantage especially for use at low frequencies and / or for applications that must be customized considering that they can virtually operate starting by dc.

gain - fr	equency	NF	P 1dB	IP3	IP2	reverse	pwr.		
optimal	max		I IGD			insul.	supply	cod	
dB MHz	dB MHz	dB MHz	dBm	dBm	dBm	dB	V mA	cou.	GPA GPD CGY21
20 100 - 900	15 30 - 2000	3.9 100 - 900	+ 19	+ 32			4.5 160	CGY 21	TO39 case with small heat sink 9 x 21 mm
15 0.1 - 400	12 01 - 850	4 0.1 - 400	- 2	+ 12	+ 14		2.5 10	GPD 110	group delay 0.3 nS
15 5 - 400	12 3 - 800	4 - 4.5 5 - 400	- 2	+ 10		> 20	15 10	GPD 401 GPD 461 #	low noise RX stage or driver
14 5 - 400	12 - 800	5.5 - 6 5 - 400	+ 7	+ 19	+ 25	> 20	15 24	GDP 402 GPD 462 #	intermediate stage
15 10 - 400	13 - 900	5.5 5 - 400	+ 23	+35 / +30	+ 34	> 20	15 90	GPD 405	high power with still fair NF
8 dc - 1000		6.7	+11.5	+ 17	+ 27		3 30	MWA 320 #	group delay < 0.6 ns Imd - 58dB out 1 mW, In+Out VSWR typ. 1.5:1
6.2 dc - 1000		9	+15.2	+ 25	+31		4-5 60-80	MWA 330 #	group delay < 0.6 ns Imd - 62dB out 5 mW, In+Out VSWR typ. 1.5:1
10.5 10 - 1000	8.5 - 1300	2 - 3 10 - 1000	+ 8	+ 20	+ 28	16 - 17	15 25	UTO 1043R	High Reliability version
10 500 - 2000	9.5 400 - 2100	4.5 500-2000	+ 21	+ 33		16 - 17	15 100	UTO 2013	typical group delay 0.5 nS

MMICs with dc-block	capacitors already inside	<b>NOTE #</b> MMICs without dc-block capacitors already inside (to add externally)					
CGY 21 GPD 110 GPD 401 GPD 402 GPD 405 UTO 1043R UTO 2013	RF in cap. int.	RF in cap. ext.	GPD 461 GPD 462 MWA 320 MWA 330				

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